



Technical Data Sheet

3mm Phototransistor T-1

PT204-6B

Features

- Fast response time
- High photo sensitivity
- Pb Free
- The product itself will remain within RoHS compliant version.



Descriptions

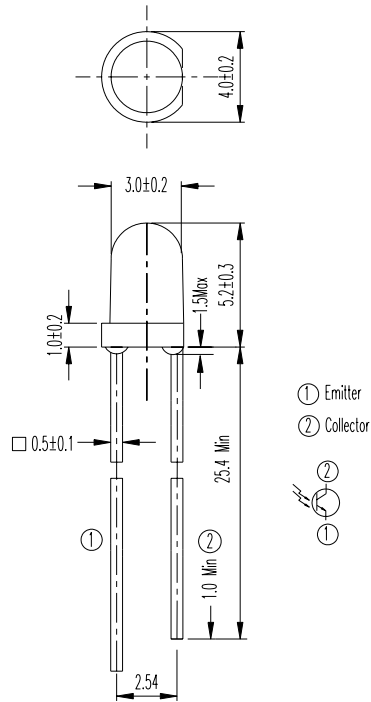
- PT204-6B is a high speed and high sensitive NPN silicon phototransistor molded in a standard 3 mm package. Due to its black epoxy the device is sensitive to infrared radiation.

Applications

- Infrared applied system
- Camera
- Printer
- Cockroach catcher

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PT204-6B	Silicon	Black

Package Dimensions


- Notes:** 1.All dimensions are in millimeters
 2.Tolerances unless dimensions $\pm 0.25\text{mm}$

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85°C	°C
Storage Temperature	T_{stg}	-40 ~ +85°C	°C
Lead Soldering Temperature	T_{sol}	260	°C
Power Dissipation at (or below) 25°C Free Air Temperature	P_c	75	mW

Notes: *1:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\ \mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100\ \mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	t_r	$V_{CE}=5V$ $I_C=1mA$	---	15	---	μS
Fall Time	t_f	$RL=1000\ \Omega$	---	15	---	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.7	---	5.07	mA
Wavelength of Peak Sensitivity	λ_p	---	---	940	---	nm
Rang of Spectral Bandwidth	$\lambda_{0.5}$	---	---	760-1100	---	nm

Rankings

Parameter	Symbol	Min	Max	Unit	Test Condition
G	$I_{C(ON)}$	0.7	1.9	mA	$V_{CE}=5V$ $E_e=1mW/c\ m^2$
H		1.14	2.6		
J		1.77	3.61		
K		2.67	5.07		

Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs. Ambient Temperature

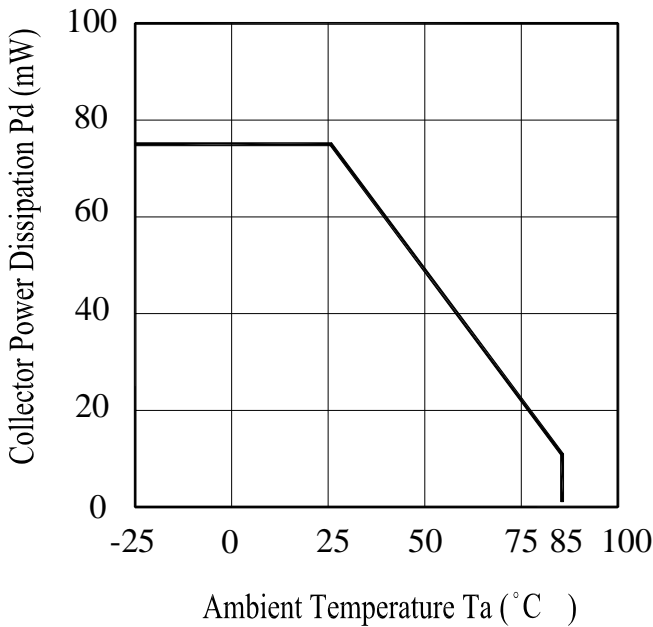


Fig.2 Spectral Sensitivity

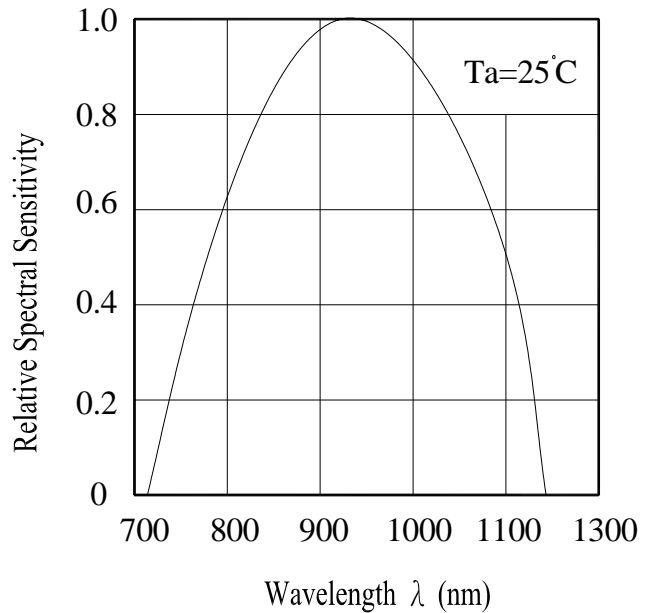


Fig.3 Relative Collector Current vs. Ambient Temperature

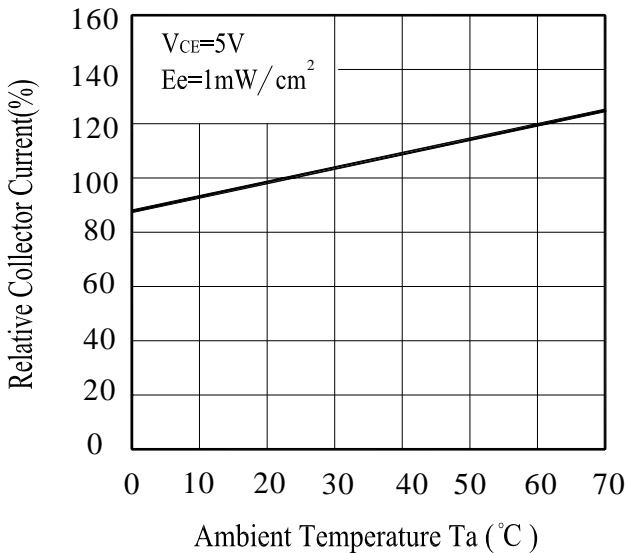
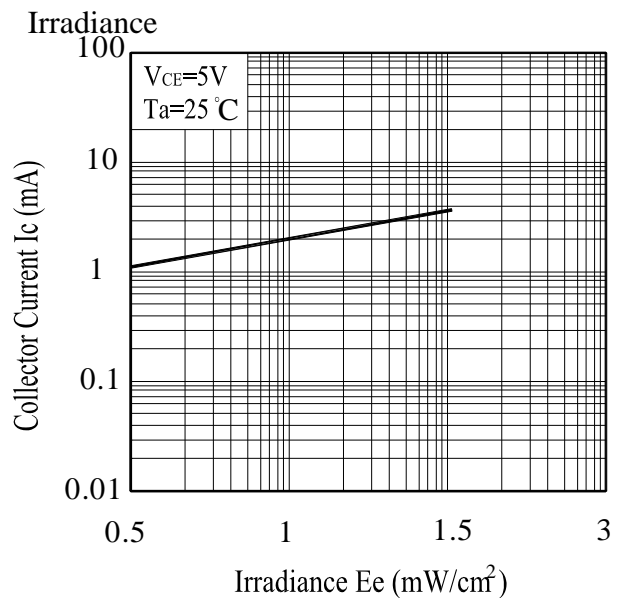


Fig.4 Collector Current vs. Irradiance



Typical Electro-Optical Characteristics Curves

Fig.5 Collector Dark Current vs. Ambient Temperature

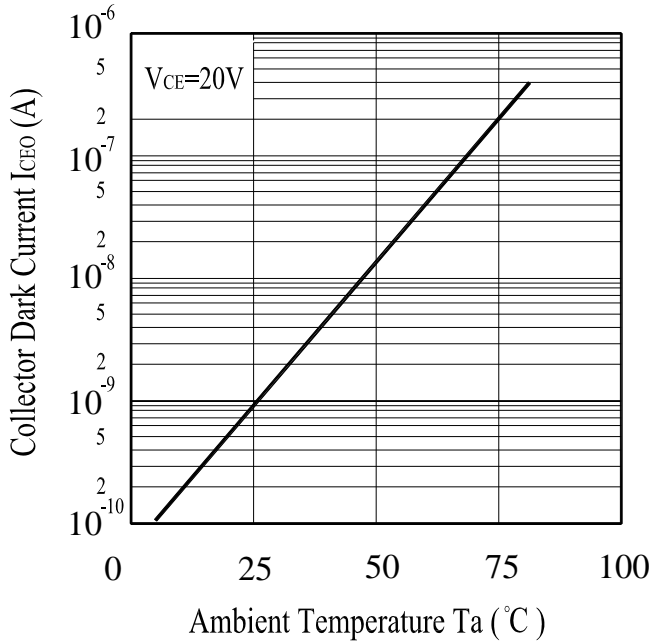
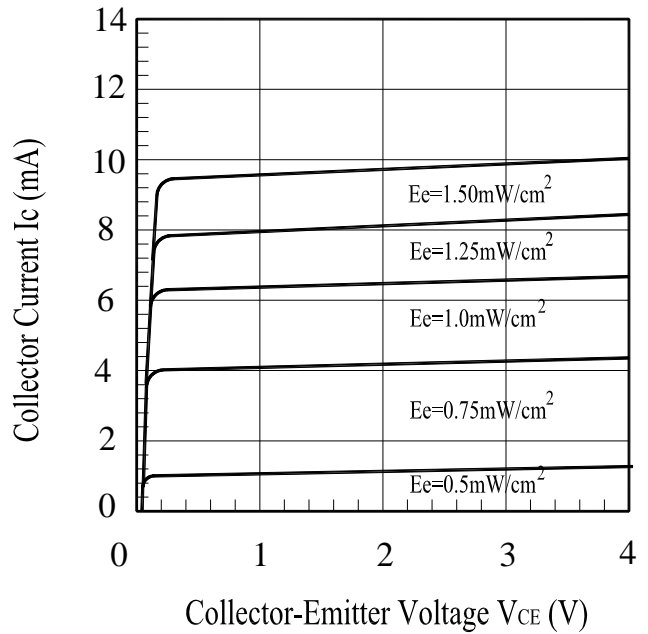


Fig.6 Collector Current vs. Collector-Emitter Voltage



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : 260°C±5°C	10secs	22pcs	$I_{C(ON)} \leq L \times 0.8$ L : Lower Specification Limit	0/1
2	Temperature Cycle	H : +100°C 15mins ↑ 5mins ↓ L : -40°C 15mins	300Cycles	22pcs		0/1
3	Thermal Shock	H : +100°C 5mins ↑ 10secs ↓ L : -10°C 5mins	300Cycles	22pcs		0/1
4	High Temperature Storage	TEMP. : +100°C	1000hrs	22pcs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs		0/1
6	DC Operating Life	V _{CE} =5V	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1

